

<b>L Numb r</b>	<b>Hits</b>	<b>S arch T xt</b>	<b>DB</b>	<b>Tim stamp</b>
-	2211	359/223-226,290-291. cls.	USPAT; US-P PUB; EPO; JPO; DERWENT	2004/06/21 07:42
-	32998	MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:42
-	6064	bimorph	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:45
-	28	359/223-226,290-291.ccls. and MEMS and bimorph	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:44
-	252225	silicon and aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:44
-	35	bimorph same (silicon and aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:45
-	240891	silicon with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:46
-	52713	substrate with groove	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:48
-	483823	etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:48
-	404	359/223-226,290-291.ccls. and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 07:48
-	1	(359/223-226,290-291.ccls. and MEMS) and (bimorph same (silicon and aluminum))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:06
-	73242	nitride with film	USPAT; US-P PUB; EPO; JPO; DERWENT	2004/06/21 08:06

-	36	(359/223-226,290-291.c ls. and MEMS) and (nitride with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:08
-	2	((359/223-226,290-291. ls. and MEMS) and (nitride with film)) and (substrat with groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:08
-	15	(359/223-226,290-291.ccls. and MEMS) and (substrate with groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:57
-	97575	etch\$4 with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:57
-	110827	potassium near2 hydroxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:58
-	60660	hydrazine	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:58
-	2461	((potassium near2 hydroxide) or hydrazine) same (etch\$4 with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:58
-	32	((((potassium near2 hydroxide) or hydrazine) same (etch\$4 with silicon)) and 359/223-226,290-291.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/21 08:58